

## Publication list Elisabeth Müller

1. **High-resolution non-destructive three-dimensional imaging of integrated circuits**  
M. Holler, M. Guizar-Sicairos, E.H.R. Tsai, R. Dinapoli, E. Müller, O. Bunk, J. Raabe, and G. Aeppli  
Nature 543 (2017) 401-407
2. **Performance-Enhancing Asymmetric Separator for Lithium-Sulfur Batteries**  
J. Conder, A. former-Cuenca, E. Müller Gubler, L. Gubler, P. Novak, and S. Trubesinger  
Appl. Materials and Interfaces **8** (2016) 18822-18831
3. **GaAs/Ge crystals grown on Si substrates patterned down to the micron scale**  
A. G. Taboada, M. Menuna, M. Salvalaglio, F. Isa, T. Kreiliger, C.V. Falub, E. Barthazy Meier, E. Müller, L. Miglio, G. Isella, and H. von Känel  
J. Appl. Phys. **119** (2016) 055301
4. **Fabrication and characterization of high-efficiency double-sided blazed x-ray optics**  
I. Mohacsi, I. Vartiainen, M. Guizar-Sicairos, P. Karvinen, V.A. Guzenko, E. Müller, C.M. Kewish, A. Somogyi, and C. David  
Optics Letters **41** (2016) 281-284
5. **Three-dimensional G/SiGe multiple quantum wells deposited on Si(001) and Si (111) patterned substrates**  
F. Isa, F. Pezzoli, G. Isella, M. Meduna, C.V. Falub, E. Müller, T. Kreiliger, A.G. Taboada, H. von Känel and L. Miglio  
Semicond. Sci. Technol. **30** (2015)105001-105010
6. **Element-Specific X-Ray Phase Tomography of 3D Structures at the Nanoscale**  
C. Donnelly, M. Guizar-Sicairos, V. Scagnoli, M. Holler, T. Huthwelker, A. Menzel, I. Vartiainen, E. Müller, E. Kirk, S. gliga, J. Raabe, L.H. Heyderman  
Phys. Rev. Lett.**114** (2015) 115501
7. **High resolution double-sided diffractive optics for hard X-ray microscopy**  
I. Mohacsi, I. Vartiainen, M. Guizar-Sicairos, P. Karvinen, V.A. Guzenko, E. Müller, E. Färm, M. Ritala, C.M. Kewish, A. Somogyi and C. David  
Optics Express **23** (2015) 776-786
8. **SiGe quantum dot crystals with periods down to 35 nm**  
D. Dais, G. Mussler, T. Fromherz, E. Müller, H.H. Solak and D. Grützmacher  
Nanotechnology **26** (2015) 255302
9. **Ge/SiGe quantum wells on Si(111): Growth, structural, and optical properties**  
E. Gatti, F. Isa, D. Chrastina, E. Müller Gubler, F. Pezzoli, E. Grilli, and G. Isella,  
J. Appl. Phys. **116** (2014) 043518
10. **Prospects for SiGe thermoelectric generators**  
A. Samarelli, L. Ferre Llin, S. Cecchi, J. Frigerio, D. Chrastina, G. Isella, E. Müller Gubler, T.

Tzelstorfer, J. Stangl, Y. Zhang, J.M.R. Weaver, P.S. Dobson, D.J. Paul  
Solid-State Electronics **98** (2014) 70-74

11. **Thin SiGe virtual substrates for Ge heterostructures integration on silicon**  
S. Cecchi, E. Gatti, D. Chrastina, J. Frigerio, E. Müller Gubler, D.J. Paul, M. Guzzi and G. Isella  
J. Appl. Phys. **115** (2014) 093502
12. **3D heteroepitaxy of mismatched semiconductors on silicon**  
C.V. Falub, T. Keiliger, F. Isa, A.G. Taboada, M. Meduna, F. Pezzoli, R. Bergamaschini, A. Marzegalli, E. Müller, D. Chrastina, G. Isella, A. Neels, P. Niedermann, A. Dommann, L. Miglio, H. von Känel  
Thin Solid Films **557** (2014) 42-49
13. **The thermoelectric properties of Ge/SiGe modulation doped superlattices**  
A. Samarelli, L. Ferre Llin, S. Cecchi, J. Frigerio, T. Etzelstorfer, E. Müller, Y. Zhang, J. R. Watling, D. Chrastina, G. Isella, J. Stangl, J.P. Hague, J.M.R. Weaver, P. Dobson, and D.J. Paul  
J. Appl. Phys. **113** (2013) 233704
14. **Fate and transformation of silver nanoparticles in urban wastewater systems**  
R. Kaegi, A. Voegelin, Ch. Ort, B. Sinnet, B. Thalmann, J. Krismer, H. Hagendorfer, M. Elumelu, E. Mueller  
WATER RESEARCH **47** (2013) 3866-3877
15. **Ge/SiGe Superlattices for Thermoelectric Devices Grown by Low-Energy Plasma-Enhanced Chemical Vapor Deposition**  
S. Cecchi, T. Etzelstorfer, E. Mueller, A. Samarelli, L. Ferre Llin, D. Chrastina, G. Isella, J. Stangl, J.M.R. Weaver, P. Dobson, and D.J. Paul  
J. ELECTRONIC MATERIALS **42** (2013) 2030-2034
16. **Self-aligned Ge and SiGe three-dimensional epitaxy on dense Si pillar arrays**  
R. Bergamaschini, F. Isa, C.V. Falub, P. Niedermann, E. Müller, G. Isella, H. von Känel, L. Miglio  
Surface Science Reports **68** (2013)390-417
17. **Phase-contrast imaging in aberration-corrected scanning transmission electron microscopy**  
F. Krumeich, E. Mueller, R.A. Wepf,  
MICRON **49** (2013) 1-14
18. **Ge/SiGe superlattices for thermoelectric energy conversion devices**  
S. Cecchi, T. Etzelstorfer, E. Müller, A. Samarelli, L. Ferre Llin, D. Chrastina, G. Isella, J. Stangl, and D.J. Paul  
J. Mat. Sci. **48** (2013) 2829-2835
19. **Prospects for SiGe Thermoelectric Generators**  
D.J. Paul, A. Samarelli, L. Ferre Llin, J.R. Watling, Y. Zhang, J.M.R. Weaver, P. Dobson, S. Cecchi, J. Frigerio, F. Isa, D. Chrastina, G. Isella, T. Etzelstorfer, J. Stangl, E. Müller Gubler  
14th International Conference on Ultimate Integration on Silicon (ULIS), Univ Warwick, Coventry, ENGLAND, MAR 19-21, 2013  
Book Series: International Conference on Ultimate Integration on Silicon (2013) 5-8

20. **Unexpected Dominance of Vertical Dislocations in High-Misfit Ge/Si(001) Films and Their Elimination by Deep Substrate Patterning**  
A. Marzegalli, F. Isa, H. Groiss, E. Müller, C.V. Falub, A. G. Taboada, P. Niedermann, G. Isella, F. Schäffler, F. Montalenti, H. von Känel, L. Miglio  
Advanced Materials **25** (2013) 4408-4412
21. **Crystallization of 8 mol% yttria-stabilized zirconia thin-film deposited by RF-sputtering**  
R. Frison, S. Heiroth, J.L.M. Rupp, K. conder, E.J. Barthazy, E. Müller, M. Horisberger, M. Döbeli, L.J. Gauckler  
Solid State Ionics **232** (2013) 29-36
22. **Ge/SiGe superlattices for nanostructured thermoelectric modules**  
D. Chrastina, S. Cecchi, J.P. Hague, J. Frigerio, A. Samarelli, L. Ferre Llin, D.J. Paul, E. Müller, T. Etzelstorfer, J. Stangl, G. Isella  
4th International Conference on Nanostructures Self-Assembly (NANOSEA), ITALY, JUN 25-29, 2012  
Thin Solid Films **543** (2013) 153-156
23. **Scaling Hetero-Epitaxy from Layers to Three-Dimensional Crystals**  
C.V. Falub, H. von Känel, F. Isa, R. Bergamaschini, A. Marzegalli, D. Chrastina, G. Isella, E. Müller, P. Niedermann, L. Miglio  
Science **335** (2012) 1330–1334
24. **The structure of dodecagonal (Ta,V)1.6Te imaged by phase-contrast scanning transmission electron microscopy**  
F. Krumeich, E. Müller, R.A. Wepf, M. Conrad, C. Reich, B. Harbrecht, R. Nesper  
J.Solid State Chemistry **194** (2012) 106–112
25. **Tensile strained Ge quantum wells on Si substrate: Post-growth annealing versus low temperature re-growth**  
M.J. Sueess, L. Carroll, H. Sigg, A. Diaz, D. chrastina, G. Isella, E. Müller, R. Spolenak  
Mat. Sci. Engineering. **B 177** (2012) 696-699
26. **Space-filling Arrays of Three-Dimensional Epitaxial Ge and Si 1-xGe x Crystals**  
C.V. Falub, F. Isa, T. Kreiliger, R. Bergamaschini, A. Marzegalli, A.G. Taboada, D. Chrastina, G. Isella, E. Müller, P. Niedermann, A. Dommann, A. Neels, A. Pezous, M. Meduna, L. Miglio, and H. Von Känel  
2012 International Silicon-Germanium Technology and Device Meeting; Berkeley, CA, USA; 4-6 June 2012 (2012) 2
27. **Investigation of diesel ash particulate matter: A scanning electron microscope and transmission electron microscope study**  
A. Liati, P. Dimopoulos Eggenschwiler, E. Müller Gubler, D. Schreiber, M. Aguirre  
Atmospheric Environment **49** (2012) 391–402
28. **Characterization of Catalysts in an Aberration-Corrected Scanning Transmission Electron Microscope**  
F. Krumeich, E. Müller, R. A. Wepf, and R. Nesper  
J. Phys. Chem. **C 115** (2011) 1080–1083

29. **Minimization of amorphous layer in Ar-ion milling for UHR-EM**  
M.J. Süess, E. Mueller, R. Wepf  
Ultramicroscopy **111** (2011) 1224–1232
30. **Crystallization and grain growth characteristics of yttria-stabilized zirconia thin films grown by pulsed laser deposition**  
S. Heiroth, R. Frison, J. L.M. Rupp, T. Lippert, E.J. Barthazy Meier, E. Müller Gubler, M. Döbeli, K. conder, A. Wokaun, L.J. Gaukler  
Solid State Ionics **191** (2011) 12-23
31. **Current quantization in an optically driven electron pump based on self-assembled quantum dots**  
L. Nevou, V. Liverini, P. Friedli, F. castellano, A. Bismuto, H. Sigg, F. Gramm, E. Müller, J. Faist  
Nature Physics **7** (2011) 423-427
32. **Release of silver nanoparticles from outdoor facades**  
R. Kaegi, B. Sinnet, S. Zuleeg, H. Hagendorfer, E. Mueller, R. Vonbank, M. Boller, M. Burkhardt  
Environmental Pollution **158** (2010) 2900–2905
33. **Investigation of the local Ge concentration in Si/SiGe nanostructures by convergent-beam electron diffraction**  
E. Ruh, E. Mueller, G. Mussler, H.C. Sigg, D. Gruetzmacher  
Ultramicroscopy **110** (2010) 1255–1266
34. **Fully automatic stitching and distortion correction of transmission electron microscope images**  
V. Kaynig, B. Fischer, E. Müller, J. M. Buhmann  
Journal of Structural Biology **171** (2010) 163–173
35. **Real surface area measurements of Pt<sub>3</sub>Co/C catalysts**  
H. Schulenburg, J. Durst, E. Müller, A. Wokaun, G.G. Scherer  
Journal of Electroanalytical Chemistry **642** (2010) 52–60
36. **Si/SiGe quantum cascade superlattice designs for terahertz emission**  
G. Matmon, D.J. Paul, L. Lever, M. Califano, Z. Ikonic, R.W. Kelsall, J. Zhang, D. Chrastina, G. Isella, H. von Känel, E. Mèller, and A. Neels  
J. Appl. Phys. **107** (2010) 053109
37. **Formation of Self Assembled PbTe Quantum Dots in CdTe on Si(111)**  
F. Felder, A. Fognini, M. Rahim, M. Fill, E. Müller, H. Zogg  
Edited by: J. Nitta, J; H. Munekata, Proc. 14<sup>th</sup> int. conf. on narrow gap semiconductors and systems Book Series: Physics Procedia **3**, Issue: 2 (2010) 1121-1125
38. **Impact of misfit dislocations on wavefront distortion in Si/SiGe/Si optical waveguides**  
A. Trita, F. Bragheri, I. Cristiani, V. Degiorgio, D. Chrastina, D. Colombo, G. Isella, H. von Känel, F. Gramm, E. Müller, M. Döbeli, E. Bonera, R. Gatti, F. Pezzoli, E. Grilli, M. Guzzi, L. Miglio  
Optics Communications **282** (2009) 4716-4722
39. **Microscopical Investigations of PEDOT:PSS Thin Films**  
U. Lang, E. Mueller, N. Naujoks, J. Dual  
ADV. FUNCTIONAL MAT. **19** (2009) 1215-1220

40. **Heat-Treated PtCo<sub>3</sub> Nanoparticles as Oxygen Reduction Catalysts**  
H. Schulenburg, E. Müller, G. Khelashvili, T. Roser, H. Bönemann, A. Wokaun, G.G. Scherer;  
*J. Phys. Chem. C* **113** (2009), 4069
41. **3D SiGe Quantum Dot Crystals: Structural Characterization and Electronic Coupling**  
T. Fromherz, J. Stangl, R.T. Lechner,  
18th International Conference on High Magnetic Fields in Semiconductor Physics and  
Nanotechnology, Sao Pedro, Brazil, AUG 03-08, 2008  
*Int. J. Modern Physics B* **23** (2009) 2836-2841
42. **X-ray diffraction investigation of a three-dimensional Si/SiGe quantum dot crystal**  
V. Holy, J. Stangl, T. Fromherz, R.T. Lechner, E. Wintersberger and G. Bauer  
*Phys. Rev. B* **79** (2009) 035324
43. **Impact of template variations on shape and arrangement of Si/Ge quantum dot arrays,**  
C. Dais, H. H. Solak, E. Müller, and D. Grützmacher  
*Appl. Phys. Lett.* **92**, (2008) 143102
44. **Magnetic metastability in natural hemo-ilmenite solid solution ( $y$  approximate to 0.83);**  
A.U. Gehring, G. Mastrogiacomo, H. Fischer, G. Weidler, E. Muller, J. Luster; *J. Magn.*  
*Mater.* **320**, (2008) 3307
45. **Removal of oxide nanoparticles in a model wastewater treatment plant: Influence of  
agglomeration and surfactants on clearing efficiency;**  
L.K. Limbach, R. Bereiter, E. Mueller, R. Krebs, R. Gaelli, W.J. Stark;  
*Environ. Sci. Technol.*, **42**, (2008) 5828
46. **Electrochemical surface reshaping of polycrystalline platinum: Morphology and  
crystallography;**  
X. Wei, A. Reiner, E. Muller, A. Wokaun, G.G. Scherer, L. Zhang, K.Y. Shou, B.J. Nelson;  
*Electrochim. Acta*, **53**, (2008) 4051
47. **Investigation of the Local Ge Concentration in Si/SiGe Multi-QW Structures by CBED  
Analysis and FEM Calculations;**  
E. Ruh, E. Müller, G. Mussler, K. Ensslin, D. Grützmacher; *Microscopy of Semiconductor  
Materials 2007*, Proceedings of 15th conference, Cambridge, UK, Springer Proceedings in  
Physics; (2008) 111
48. E. Ruh, E. Müller, G. Mussler, D. Grützmacher; 14th European Microscopy Congress, EMC  
2008 Aachen, Germany, (eds. Luysberg, M., Tillmann, K. & Weirich, T.)  
*Proc. Vol. 1*, (2008) 225
49. **EELS/EFTEM in life science: proof of the presence of H<sub>2</sub>O<sub>2</sub> in human skin by Ce  
deposition in melanosomes;**  
E. Müller, M.S. Lucas, K. Mätzold, R. Wepf; 14th European Microscopy Congress, EMC 2008  
Aachen, Germany. (eds. Luysberg, M., Tillmann, K. & Weirich, T.)  
*Proc. Vol. 1* (2008) 413
50. **Tunable few-electron quantum dots in InAs nanowires;**  
I. Shorubalko, A. Pfund, R. Leturcq, M.T. Borgstrom, F. Gramm, E. Müller, E. Gini, K. Ensslin;  
*Nanotechnology* **18**, (2007) 4

51. **Unveiling the morphology of buried In(Ga)As nanostructures by selective wet chemical etching: From quantum dots to quantum rings;**  
F. Ding, L. Wang, S. Kiravittaya, E. Müller, A. Rastelli and O. G. Schmidt;  
Appl. Phys. Lett. **90**, 173104 (2007)
52. **All-GaInNAs ultrafast lasers: Material development for emitters and absorbers;**  
A. Rutz, V. Liverini, E. Müller, S. Schön, U. Keller;  
J. Crystal Growth **301–302**, (2007) 525
53. **Templated self-organization of SiGe quantum structures for nanoelectronics;**  
D. Grützmacher, Ch. Dais, L. Zhang, E. Müller, H. H. Solak;  
Mat. Science and Engineering **C 27**, (2007) 947
54. **Three-dimensional Si/Ge quantum dot crystals**  
D. Grützmacher, T. Fromherz, C. Dais, J. Stangl, E. Müller, Y. Ekinci, H.H. Solak, H. Sigg, R.T. Lechner, E. Wintersberger, S. Birner, V. Holy, and G. Bauer  
Nano Letters **7** (2007) 3150-3156
55. **Analysis of strain relaxation by microcracks in epitaxial GaAs grown on Ge/Si substrates;**  
D. Colombo, E. Grilli, M. Guzzi, S. Sanguinetti, S. Marchionna, and M. Bonfanti, A. Fedorov, H. von Känel, and G. Isella, E. Müller;  
J. Appl. Phys. **101**, (2007) 103519
56. **Tunable lateral tunnel coupling between two self-assembled InGaAs quantum dots;**  
G. J. Beirne, C. Hermannstädter, L. Wang, A. Rastelli, E. Müller,  
O. G. Schmidt, and P. Michler;  
Conf. Proc. Ultrafast Phenomena in Semiconductors and Nanostructure Materials XI and  
Semiconductor Photodetectors IV, San Jose, CA, USA, 2007;  
SPIE Proceedings **6471**, (2007) 647104-1-13
57. **TEM Study of Zirconia Inclusions in Natural Ilmenite Crystals;**  
E. Müller, A.U. Gehring;  
Microscopy Conference 2007, Saarbrücken, Germany, 2007  
Proc. Microsc. Conf. (2007) 372
58. **Ge quantum dot molecules and crystals: Perparation and Properties**  
C. Dais, H.H. Solak, Y. Ekinci,  
Conference: International Conference on NANO-Structures Self Assembling, Aix en Provence,  
France, JUL 02-06, 2006  
Surface Science **601** (2007) 2787-2791
59. **Templated self-organization of SiGe quantum structures for nanoelectronics**  
D. Gruetzmacher, C. Dais, L. Zhang, E. Muller, H.H. solak  
Symposium on Current Trends in Nanoscience - From Materials to Applications, E-MRS Spring  
Meeting, Nice, FRANCE, MAY 29-JUN 02, 2006  
Mat. Sci. Eng. **C27** (2007) 947-953
60. **characterization of Ta and TaN diffusion barriers beneath Cu layers using picosecond ultrasonics;**

J. Bryner, D. M. Profunser, J. Vollmann, E. Mueller, J. Dual;  
Ultrasonics **44**, (2006) e1269

61. **Tuning the intersubband absorption in strained AlAsSb/InGaAs quantum wells towards the telecommunications wavelength range;**  
P. Cristea, Y. Fedoryshyn, J.F. Holzman, F. Robin, H. Jäckel, E. Müller and J. Faist;  
J. Appl. Phys. **100**, (2006) 116104
62. **Evolution of buried semiconductor nanostructures and origin of stepped surface mounds during capping;**  
G. Katsaros, A. Rastelli, M. Stoffel, G. Costantini, O.G. Schmidt, K. Kern, J. Tersoff, E. Müller and H. von Känel;  
Appl. Phys. Lett. **89**, (2006) 253105
63. **Photoemission electron microscopy study of remanent magnetic domain states in ferromagnetic wedge films deposited on substrates with micrometer-sized square plateaus;**  
L.J. Heyderman, S. Czekaj, F. Nolting, E. Müller, P. Fischer, Ph. Gasser and L. Lopez-Diaz;  
J. Appl. Phys. **99**, (2006) 63904
64. **Highly reflective AlGaAsSb/InP Bragg reflector at 1.55µm grown by MOVPE**  
O. Ostinelli, M. Haiml, R. Grange, G. Almuneau, M. Ebnöther, E. Gini, E. Müller, U. Keller, W. Bächtold  
J. Crystal Growth **286** (2006) 247-254
65. **Thin relaxed SiGe virtual substrates grown by low-energy plasma-enhanced chemical vapor deposition;**  
D. Chrastina, G. Isella, M. Bollani, B. Rössner, E. Müller, T. Hackbarth, E. Wintersberger, Z. Zhong, J. Stangl and H. von Känel;  
J. Crystal Growth **281**, (2005) 281
66. **Structural studies of strain-symmetrised modulation-doped Si/SiGe structures grown by molecular beam epitaxy;**  
C.V. Falub, M. Meduna, E. Müller, S. Tsujino, A. Borak, H. Sigg, D. Grützmacher, T. Fromherz and G. Bauer;  
J. Crystal Growth **278**, (2005) 495
67. **Optically Bright Quantum Dots in Single Nanowires;**  
M. T. Borgstrom, V. Zwiller, E. Müller and A. Imamoglu;  
Nano Letters **5**, (2005) 1439
68. **Transport and absorption in strain-compensated Si/Si<sub>1-x</sub>Ge<sub>x</sub> multiple quantum well and cascade structures deposited on Si<sub>0.5</sub>Ge<sub>0.5</sub> pseudosubstrates;**  
D. Grützmacher, S. Tsujino, C. Falub, A. Borak, L. Diehl, E. Müller, H. Sigg, U. Gennser, T. Fromherz, M. Meduna, G. Bauer, J. Faist and O. Kermarrec;  
Materials Science in Semiconductor Processing **8**, (2005) 401
69. **Bandstructure analysis of strain compensated Si/SiGe quantum cascade structures;**  
H. Sigg, C.V. Falub, E. Müller, A. Borak, D. Grützmacher, T. Fromherz, M. Meduna and O.

Kermarrec;  
Optical Materials **27**, (2005) 841

70. **Al substitution in MgB<sub>2</sub> crystals: Influence on superconducting and structural properties;**  
J. Karpinski, N.D. Zhigadlo, G. Schuck, S.M. Kazakov, B. Batlogg, K. Rogacki, R. Puzniak, J. Jun, E. Müller, P. Wägli, R. Gonnelli, D. Daghero, G.A. Ummarino, V.A. Stepanov and P.N. Lebedev;  
Phys. Rev. **B.71**, (2005) 174506
71. **High temperature investigations of Si/SiGe based cascade structures using x-ray scattering methods;**  
M. Meduna, J. Novak, C.V. Falub, G. Chen, G. Bauer, S. Tsujino, D. Grützmacher, E. Müller, Y. Campidelli, O. Kermarrec, D. Bensahel and N. Schell;  
J. Physics **D 38**, (2005) A121
72. **Interface-roughness-induced broadening of intersubband electroluminescence in p-SiGe and n-GaInAs/AlInAs quantum-cascade structures;**  
S. Tsujino, A. Borak, E. Müller, M. Scheinert, C.V. Falub, H. Sigg, D. Gützmacher, M. Giovannini and J. Faist;  
App. Phys. Lett. **86**, (2005) 62113
73. **Recent results on the road to a SiGe quantum cascade laser;**  
A. Borak, S. Tsujino, C. Falub, et al.; Group-IV Semiconductor Nanostructures. Symposium, 2004, Boston, MA, USA;  
Mat. Res. Soc. Symposium Proc. **832**, (2005) 69
74. **Recent Results on the Road to a SiGe Quantum Cascade Laser;**  
A. Borak, S. Tsujino, H. Sigg, C. V. Falub, M. Scheinert, L. Diehl, D. Grützmacher, E. Müller, U. Gennser, Y. Campidelli, O. Kermarrec, D. Bensahel, and J. Faist;  
Mater. Res. Symp. Proc. Vol. **832**, (2005) F4.2.1-14.
75. **Mapping and analysis of microscopic Seebeck coefficient distribution;**  
H.L. Ni, X.B. Zhao, G. Karpinski, et al.;  
J. Mat. Science **40**, (2005) 605
76. **Dislocation density and structure in Si<sub>1-x</sub>Ge<sub>x</sub> buffer layers deposited by LEPECVD;**  
M. Bollani, E. Muller, G. Isella, S. Signoretti, D. Chrastina, H. von Kanel,  
Ed. A.G. Cullis, P.A. Midgley; Microscopy of Semiconducting Materials Conference, 2003, Cambridge, UK; Inst. of Phys. Conf. Series **180**, (2004) 247
77. **High quality SiGe electronic material grown by low energy plasma enhanced chemical vapour deposition**  
D. Chrastina, G. Isella, B. Rossner, M. Bollani, E. Muller, T. Hackbarth, H. von Kanel; 8th European Vacuum Conference & the 2nd Annual Conference of the German Vacuum Society, 2003, Berlin, Germany;  
Thin Solid Films **459**, (2004) 37
78. **Resonant tunneling in Si-SiGe superlattices on relaxed buffer substrates**  
S. Tsujion, S. Mentese, L. Diehl, E: Muller, B Haas, D. Bachle, S StutzD. Grutzmacher, Y.

Campidelli, O Kermarrec, D. Bensahel; First International SiGe Technology and Device Meeting (ISTDM 2003) From Materials and Process Technology to Device and Circuit Technology , 2003, Nagoya, Japan;  
Appl. Surf. Science **224**, (2004) 377

79. **Shape and composition change of Ge dots due to Si capping;**  
O. Kirfel, E. Muller, D. Grutzmacher, K. Kern, A. Hesse, J. Stangl, V. Holy, G. Bauer; First International SiGe Technology and Device Meeting (ISTDM 2003) From Materials and Process Technology to Device and Circuit Technology , 2003, Nagoya, Japan;  
Appl. Surf. Science **224**, (2004) 139
80. **Hall mobility of narrow Si<sub>0.2</sub>Ge<sub>0.8</sub>-Si quantum wells on Si<sub>0.5</sub>Ge<sub>0.5</sub> relaxed buffer substrates**  
S. Tsujino, C.V. Falub, E.; Muller, M. Scheinert, L. Diehl, U. Gennser, T. Fromherz, A Borak, H. Sigg, D. Grutzmacher, Y. Campidelli, O. Kermarrec, D. Bensahel;  
Appl. Phys. Lett. **84**, (2004) 2829
81. **Successful shape-preservation of Ge-clusters during Si-coverage at low temperature;**  
E. Muller, O. Kirfel, A. Rastelli, H. von Kanel, D. Grutzmacher;  
Mat. Sci.& Eng. B **101**, (2003) 142
82. **Self-assembled formation of vertical silicon-rich quantum wells and Ge/SiGe quantum wire superlattices;**  
A. Beyer, E Müller, C David, B. Haas, B Ketterer, D. Grützmacher;  
Europhysics Lett. **63**, (2003) 459
83. **Compressively strained Ge channels on relaxed SiGe buffer layers;**  
M. Bollani, E. Muller, S. Signoretti, C. Beeli, G. Isella, M. Kummer, H. von Kanel,  
Mat. Sci. & Eng. **B 101**, (2003) 102
84. **Influence of capping on strain, composition and shape of SiGe islands,**  
A. Hesse, J. Stangl, V. Holy, G. Bauer, O. Kirfel, E. Muller, D. Grutzmacher,  
Mat. Sci. & Eng. **B 101**, (2003) 71
85. **Strain-compensated Si/Si<sub>0.2</sub>Ge<sub>0.8</sub> quantum cascade structures grown on Si<sub>0.5</sub>Ge<sub>0.5</sub> pseudo-substrates;**  
S. Mentese, L. Diehl, E. Muller, H. Sigg, D. Grutzmacher, T. Roch, J. Stangl, G. Bauer, U. Gennser, I. Sagnes, Y. Campidelli, O. Kermarrec, D. Bensahel, J. Faist;  
Physica **E 17**, (2003) 613
86. **Shape transformation of Ge quantum dots due to Si overgrowth;**  
O. Kirfel, E. Muller, D. Grutzmacher, K. Kern;  
Physica **E 16**, (2003) 602
87. **Absorption measurement of strained SiGe nanostructures deposited by UHV-CVD;**  
G. Palfinger, B. Bitnar, H. Sigg, E. Muller, S. Stutz, D. Grutzmacher;  
Physica **E 16**, (2003) 481

88. **Strain compensated Si/SiGe quantum well and quantum cascade on Si<sub>0.5</sub>Ge<sub>0.5</sub> pseudosubstrate;**  
L. Diehl, S. Mentese, E. Muller, D. Grutzmacher, H. Sigg, T. Fromherz, J. Faist, U. Gennser, Y. Campidelli, O. Kermarrec, D. Bensahel;  
Physica E **16**, (2003) 315
89. **Strain compensated Si/Si<sub>0.2</sub>Ge<sub>0.8</sub> quantum cascade structures grown by low temperature molecular beam epitaxy;**  
D. Grutzmacher, S. Mentese, E. Muller, L. Diehl, H. Sigg, Y. Campidelli, O. Kermarrec, D. Bensahel, T. Roch, J. Stangl, G. Bauer;  
J. Crystal Growth **251**, (2003) 707
90. **Application of energy filtering techniques in TEM: the SiGe and the CaF<sub>2</sub>/GaAs systems,**  
E. Müller, O. Kirfel, S. Schön, D. Grützmacher;  
Third Swiss-Japanese Joint Seminar on Advanced Microscopy for Nanotechnology, 2.-6. 3. 2003, Arosa, Switzerland (INVITED TALK)
91. **Intersubband quantum cascades in the Si/SiGe material system;**  
L. Diehl, G. Dehlinger, H. Sigg, U. Gennser, D. Grützmacher, E. Müller, J. Faist, K. Ensslin, I. Sagnes, Y. Campidelli, O. Kermarrec, D. Bensahel;  
Physica-E. **13**; (2002) 829
92. **Germanium islands embedded in strained silicon quantum wells grown on patterned substrates**  
A. Beyer, E. Müller, H. Sigg, S. Stutz, C. David, K. Ensslin, D. Grützmacher;  
J. Microelectronics **33**, (2002) 525
93. **Intersubband absorption performed on p-type modulation-doped Si<sub>0.2</sub>Ge<sub>0.8</sub>/Si quantum wells grown on Si<sub>0.5</sub>Ge<sub>0.5</sub> pseudosubstrate;**  
L. Diehl, H. Sigg, G. Dehlinger, D. Grützmacher, E. Müller, U. Gennser, I. Sagnes, T. Fromherz, Y. Campidelli, O. Kermarrec, D. Bensahel, J. Faist;  
Appl. Phys. Lett. **80**, (2002) 3274
94. **Very high hole mobilities in modulation-doped Ge quantum wells grown by low-energy plasma enhanced chemical vapor deposition;**  
H. von Kanel, M. Kummer, G. Isella, E. Müller, T. Hackbarth;  
Appl. Phys. Lett. **80**, (2002) 2922
95. **Si/SiGe quantum cascade structures emitting in the 10  $\mu$  m range;**  
G. Dehlinger, L. Diehl, U. Gennser, H. Sigg, E. Müller, S. Stutz, J. Faist, J. Stangl, T. Roch, G. Bauer, D. Grützmacher;  
Mat. Sci. & Eng. **B89**, (2002) 30
96. **Low energy plasma enhanced chemical vapor deposition**  
M. Kummer, C. Rosenblad, A. Dommann, T. Hackbarth, G. Hock, M. Zeuner, E. Müller, H. von Kanel;  
Mat. Sci. & Engineering **B89**, (2002) 288

97. **Shape preservation of Ge/Si(001) islands during Si capping;**  
A. Rastelli, E. Müller, H. von Känel;  
Appl. Phys. Lett. **80**, (2002) 1438
98. **Silicon/silicon suboxide heterostructures grown by molecular beam epitaxy;**  
A. Sticht, M. Markmann, K. Brunner, G. Abstreiter, E. Müller;  
Mat. Sci. &Engineering **B89**, (2002) 274
99. **Structural and optical properties of vertically correlated Ge island layers grown at low temperatures**  
M. Herbst, C. Schramm, K. Brunner, T. Asperger, H. Riedl, G. Abstreiter, A. Vörckel, H. Kurz, E. Müller  
Mat. Sci. &Engineering **B89** (2002) 54-57
100. **Investigation of the early stages of Si-overgrowth of Ge-dots on Si (001)**  
E. Müller, O. Kirfel, A. Rastelli, H. von Kanel, D. Grützmacher  
Microscopy of Semiconducting Materials 2001. Proceedings of the Royal Microscopical Society Conference. IOP Publishing, Bristol, UK; p.163-6, 2001
101. **Valence band intersubband electroluminescence from Si/SiGe quantum cascade structures**  
H. Sigg-H, G. Dehlinger, L. Diehl, U. Gensser, S. Stutz, J. Faist, D. Grutzmacher, K. Ensslin, E. Müller  
Physica-E **11** (2001).240-4
102. **Raman spectroscopy of carbon-induced germanium dots**  
C. Guedj, A. Beyer, E. Muller, D. Grutzmacher  
Appl. Phys. Lett. **78**, p.1742-4, 2001
103. **Comparison of low temperature growth of Si thin films on amorphous substrates by MBE and PECVD methods**  
J.A.A. Selvan, D. Grutzmacher, E. Muller, M. Rebien, M. Kummer, H. von Kanel, J. Gobrecht  
Edited by: Collins, R.W.; Branz, H.M.; Stutzmann, M.; et al. Conference: Amorphous and Heterogeneous Silicon Thin Films - 2000. Symposium, San Francisco, CA, USA, 24-28 April 2000  
Materials Research Society Symposium Proceedings Vol.**609** (2001) A19.4.1-6
104. **Optical and structural analysis of Ge quantum dots embedded in strained Si quantum wells grown on patterned substrates**  
A. Beyer, E. Muller, H. Sigg,  
Edited by: Fauchet, P.M.; Buriak, J.M.; Canham, L.T.; et al.  
Microcrystalline and Nanocrystalline Semiconductors - 2000. Symposium, Boston, MA, USA, 27-30 Nov. 2000  
Materials Research Society Symposium Proceedings Vol.**638** (2001) F14.8.1-6
105. **Intersubband electroluminescence from Si/SiGe quantum cascade structures**  
G. Dehlinger, L. Diehl, U. Gensser,  
Edited by: Robbins, DJ; Trezza, JA; Jabbour, GE, Conference on Silicon-based and Hybrid Optoelectronics III, SAN JOSE, CA, JAN 23-24, 2001  
Proc. Soc. Photo optical instrumentation engineers (SPIE) **4293** (2001) 79-85

106. **Intersubband electroluminescence from silicon-based quantum cascade structures**  
G. Dehlinger, L. Diehl, U. Gennser, H. Sigg, J. Faist, K. Ensslin, D. Grutzmacher, E. Muller  
Science. **290** (2000) 2277-9
107. **Photoluminescence of carbon-induced Ge islands in silicon**  
A. Beyer; O. Leifeld; E. Muller; S. Stutz; H. Sigg; D. Grutzmacher  
Thin Solid Films. **380** (2000) 246-8
108. **Nucleation of Ge quantum dots on the C-alloyed Si(001) surface**  
O. Leifeld; A. Beyer; E. Muller; D. Grutzmacher; K. Kern  
Thin Solid Films. **380** (2000) 176-9
109. **In situ STM analysis and photoluminescence of C-induced Ge dots**  
A. Beyer; O. Leifeld; S. Stutz; E. Muller; D. Grutzmacher  
Nanotechnology. **11** (2000) 298-304
110. **Size control of carbon-induced Ge quantum dots**  
A. Beyer; E. Muller; H. Sigg; S. Stutz; D. Grutzmacher; O. Leifeld; K. Ensslin  
Appl. Phys. Lett. **77** (2000) 3218-20
111. **A simple and fast TEM preparation method utilizing the pre-orientation in plate-like, needle-shaped and tubular materials**  
E. Muller; F. Krumeich  
Ultramicroscopy. **84** (2000) 143-7
112. **Investigation of the emitter structure in SiGe/Si resonant tunneling structures**  
G. Dehlinger; U. Gennser; D. Grutzmacher; Th. Ihn; E. Muller; K. Ensslin  
Thin Solid Films. **369** (2000) 390-3
113. **Formation and ordering effects of C-induced Ge dots grown on Si(001) by molecular beam epitaxy**  
O. Leifeld; A. Beyer; E. Muller; K. Kern; D. Grutzmacher  
Materials Science & Engineering **B74**; p.222-8, 2000
114. **Structural and electrical characterization of Si-MODFET structures grown at high rates by LEPECVD**  
C. Rosenblad, M. Kummer, E. Muller, A. Dommann, H. von-Kanel  
Mat. Res. Soc. Symp. Proceedings **587** (2000) O7.9.1-6
115. **A possible production technique for modulation doped SiGe heterostructures**  
C. Rosenblad, M. Kummer, E. Muller, T. Hackbarth, H. Von-Kanel  
Mat. Res. Soc. Proceedings **585** (2000) 141-5
116. **Virtual substrates for the n- and p-type Si-MODFET grown at very high rates**  
C. Rosenblad; M. Kummer; A. Dommann; E. Muller; M. Gusso; L. Tapfer; H. von Kanel  
Mat.Science & Engineering **B74** (2000) 113-17

117. **Fast deposition process for graded SiGe buffer layers**  
H. von Kanel; C. Rosenblad; M. Kummer; E. Muller; T. Graf; T. Hackbarth  
Jap. J. Appl.Phys **39** (2000) 2050-3
118. **Strain relaxation of graded SiGe buffers grown at very high rate**  
C. Rosenblad; J. Stangl; E. Muller; G. Bauer; H. von Kanel  
Mat.Science & Engineering **B71** (2000) 20-3
119. **A plasma process for ultrafast deposition of SiGe graded buffer layers**  
C. Rosenblad; H. von Kanel; M. Kummer; A. Dommann; E. Muller  
Appl. Phys. Lett. **76** (2000) 427-9
120. **Pre-structuring of silicon substrates to investigate MBE-growth of SiGe layers**  
David-C; R. Hartmann; U. Gennser; E. Muller; D. Grutzmacher  
Microelectronic Engineering. **46** (1999) 275-8
121. **Self-organized growth of Ge quantum dots on Si(001) substrates induced by sub-monolayer C coverages**  
O. Leifeld; R. Hartmann; E. Muller; E. Kaxiras; K. Kern; D. Grutzmacher  
Nanotechnology. **10** (1999) 122-6
122. **Microscopic environment of Fe in epitaxially stabilized c-FeSi**  
M. Fanciulli; G. Weyer; A. Svane; N.E. Christensen; H. von Kanel; E. Muller; N. Onda; L. Miglio; F. Tavazza; M. Celino  
Phys.Rev. **B59** (1999) 3675-87
123. **In situ scanning tunneling microscopy study of C-induced Ge quantum dot formation on Si(100)**  
O. Leifeld; E. Muller; D. Grutzmacher; B. Muller; K. Kern  
Appl. Phys. Lett. **74** (1999) 994-6
124. **TEM study of an anti-correlation relation in corrugated layers of Si<sub>1-x</sub>Ge<sub>x</sub>/Si superlattices**  
E. Muller, R. Hartmann, D. Grutzmacher,  
Edited by: Cullis, AG; Beanland, R  
Conference on Microscopy of Semiconducting Material, Oxford, England, MAR 22-25, 1999  
Microscopy of semiconducting materials 1999,  
Proc. Book Series: Inst.Phys. conf. SERIES **164** (1999) 227-230
125. **Photoluminescence in strain compensated Si/SiGeC multiple quantum wells**  
R. Hartmann; U. Gennser; D. Grutzmacher; H. Sigg; E. Muller; K. Ensslin  
Epitaxy and Applications of Si-Based Heterostructures. Symposium.  
Mater. Res. Soc, Warrendale, PA, USA; 1998; xi+377, p.251-6, 1998
126. **Structural characterization of SiGe step graded buffer layers grown on prestructured Si[001] substrates by molecular beam epitaxy**  
E. Muller; R. Hartmann; C. David; D. Grutzmacher  
Thin Solid Films. **336** (1998) 92-5

127. **TEM study of InAs self-assembled quantum dots in GaAs**  
E. Muller, E. Ribeiro, T. Heinzl, K. Ensslin, G. Medeiros-Ribeiro, P.M. Petroff  
Symposium on Thin Films Epitaxial Growth and Nanostructure at the E-MRS Spring Meeting  
1998, Strasbourg, France  
Thin Solid Films **336** (1998) 38-4
128. **Structural characterization of SiGe step graded buffer layers grown on prestructured Si[001] substrates by molecular beam epitaxy**  
E. Muller; R. Hartmann; C. David; D. Grutzmacher  
Edited by: Kasper, E; Wang, KL; Hasegawa, H  
Symposium on Thin Films Epitaxial Growth and Nanostructures, at the E-MRS Spring Meeting  
1998, Strasbourg, France, JUN 16-19, 1998  
European Mat. Res. Soc. Sym. Proc. **79** (1999) 92-95
129. **InAs self-assembled quantum dots as controllable scattering centers near a two-dimensional electron gas**  
E. Ribeiro, E. Muller, T. Heinzl, H. Auderset, K. Ensslin, G. Medeiros-Ribeiro, and P.M. Petroff  
Phys. Rev. **B 58** (1998) 1506-1511
130. **Low temperature epitaxial growth by LEPECVD**  
C. Rosenblad, H.R. Deller, T. Graf, E. Muller, H. von Kaenel  
6th International Conference on Chemical Beam Epitaxy and Related Growth Techniques,  
Montreux, Switzerland, SEP 07-10, 1997  
J. Crystal Growth **188** (1998) 125-130
131. **Low-temperature molecular beam epitaxy of Si<sub>1-x-y</sub>Ge<sub>x</sub>C<sub>y</sub>/Si quantum well structures: electrical and optical properties**  
D. Gruetzmacher, R. Hartmann, P. Schnappauf, U. Gennser, E. Mueller, D. Baechle, A. Dommann  
7th International Symposium on Silicon Molecular Beam Epitaxy, Banff, Alta., Canada, 13-17 July 1997  
Thin Solid Films **321** (1998) 26-32
132. **Growth of Si<sub>1-y</sub>C<sub>y</sub>/Si- and Si<sub>1-x-y</sub>Ge<sub>x</sub>C<sub>y</sub>/Si multiple quantum wells using molecular beam epitaxy**  
R. Hartmann, D. Gruetzmacher, E. Muller, U. Gennser, A. Dommann, P. Schroter, P. Warren  
Symposium B on Epitaxial Thin Film Growth and Nanostructures at the ICAM/EMRS Spring Conference, Strasbourg, France, JUN 16-20, 1997  
Thin Solid Films **318** (1998) 158-162
133. **Low temperature epitaxial growth by LEPECVD**  
C. Rosenblad, H.R. Deller, M. Dobeli, E. Muller, H. von Kaenel  
Symposium B on Epitaxial Thin Film Growth and Nanostructures at the ICAM/EMRS Spring Conference, Strasbourg, France, JUN 16-20, 1997  
Thin Solid Films **318** (1998) 11-14
134. **Hydrocarbon films inhibit oxygen permeation through plastic packaging material**  
E.M. Moser, R. Urech, E. Hack, H. Kunzli, E. Muller  
Thin Solid Films **317** (1998) 388-392

135. **Competitive metastable phase in low-temperature epitaxy of CoSi<sub>2</sub>/Si(111)**  
S. Goncalves-Conto; U. Scharer; E. Muller; H. von Kanel; L. Miglio; F. Tavazza  
Phys.Rev. **B55** (1997) 7213-21
136. **Effects of substrate bias and rapid thermal processing on the luminescence of Si/SiGe multiple quantum wells grown by MBE**  
R. Hartmann, D. Grutzmacher, E. Muller, U. Gennser, A. Dommann  
European-Materials-Research-Society 1996 Spring Meeting, Symposium D: Group IV  
Heterostructures, Physics and Devices, Strasbourg, France, JUN 04-07, 1996  
Thin Solid Films **294** (1997) 50-53
137. **New epitaxially stabilized silicide phases**  
S. Goncalves-Conto; E. Muller; K. Schmidt; H. von Kanel  
Silicide Thin Films - Fabrication, Properties, and Applications. Symposium. Mater. Res. Soc,  
Pittsburgh, PA, USA; 1996; xv+648, p.493-8, 1996
138. **Structural properties of epitaxial silicide layers on Si**  
H. von Kanel; E. Muller; S. Goncalves-Conto; C. Schwarz; N. Onda  
Appl. Surf. Science. **104** (1996) 204-12
139. **Sputter epitaxy of step-graded Si<sub>1-x</sub>Ge<sub>x</sub>/Si(001): evolution of defects and surface morphology**  
P. Sutter; B. Vogeli; E. Muller; H. von Kanel; A. Dommann  
Appl. Surf. Science, **102** (1996) 33-7
140. **Magnetron sputter epitaxy of Si/Ge heterostructures**  
P. Sutter, E. Muller, S. Tao, C. Schwarz, M. filzmoser, M. Lenz, H. von Känel  
6th International Symposium on Silicon Molecular Beam Epitaxy of the 1995 E-MRS Spring  
Conference, Strasbourg, France, MAY 22-26, 1995  
J. Crystal Growth **157** (1995) 172-176
141. **Quantum transport in sputtered, epitaxial Si/Si<sub>1-x</sub>Ge<sub>x</sub> heterostructures**  
P. Sutter; D. Groten; E. Muller; M. Lenz; H. von Kanel  
Appl. Phys. Lett. **67** (1995) 3954-6, OJPS Article <http://link.aip.org/link/?APL/67/3954>, 1995
142. **New epitaxially stabilized CoSi phase with the CsCl structure**  
H. von Kanel; C. Schwarz; S. Goncalves-Conto; E. Muller; L. Miglio; F. Tavazza; Malegori-G  
Phys. Rev. Lett. **74**, (1995) 1163-6  
  
Phys Rev Article <http://publish.aps.org/abstract/PRL/v74/p1163>, 1995
143. **TEM Investigation of Iron Disilicide Films on Si(001) Grown by Molecular-Beam Epitaxy**  
H.U. Nissen, E. Müller, H.H. Deller, and H. von Känel  
Physica Status Solidi A **150** (1995) 395-406
144. **Epitaxial semiconducting and metallic iron silicides**  
  
H. von Kanel; U. Kafader; P. Sutter; N. Onda; H. Sirringhaus; E. Muller; U. Kroll; C. Schwarz;  
S. Concalves-Conto

Silicides, Germanides, and Their Interfaces. Symposium. Mater. Res. Soc, Pittsburgh, PA, USA; 1994; xi+497 pp, p.73-84, 1994

145. **Magnetron sputter epitaxy of Si/sub m/Ge/sub n//Si(001) strained-layer superlattices**  
P. Sutter; C. Schwarz; E. Muller; V. Zelezny; S. Goncalves-Conto; H. von Kanel  
Appl. Phys. Lett. **65**, (1994) 2220-2  
OJPS Article <http://link.aip.org/link/?APL/65/2220>, 1994
146. **High-resolution transmission electron microscopic study of the gamma -FeSi/sub 2//Si(111) interface**  
E. Muller; Grindatto-DP; Nissen-H-U; N. Onda; H. von Kanel  
Appl. Phys. Lett. **64**, (1994) 1938-40
147. **Fundamental Phenomena in Heteroepitaxial Growth Studied by Scanning-Tunneling-Microscopy**  
H. Siringhaus, N. Onda, E. Muller Gubler, P. Muller, S. Zehnder, H. von Kanel  
8th Int. Conf. Solid Surfaces ( ICSS-8 ) / 12TH Int. Vac. Congress ( IVC-12 ) The Hague, Netherlands, OCT 12-16, 1992  
Surf. Sci. **287** (1993) 1019-1024
148. **Phase-Transition from Pseudomorphic FeSi2 to Beta-FeSi2/Si(111) Studied by Insitu Scanning-Tunneling-Micorsocpy**  
H. Siringhaus, N. Onda, E. Muller Gubler, P. Muller, R. Stalder, H. von Kanel  
Phys. Rev. **B47** (1993) 10567-10577
149. **Structural and electronic properties of pseudomorphic FeSi/sub 1+x/ films on Si(111)**  
N. Onda; H. Siringhaus; E. Muller; H. von Kanel  
J. Crystal-Growth **127**, (1993) 634-7
150. **Structural and electronic properties of metastable epitaxial FeSi/sub 1+x/ films on Si(111)**  
H. von Kanel; K.A. Mader, E. Muller; N. Onda; H. Siringhaus  
Phys. Rev. **B45**, (1992) 13807-10
151. **Observation and characterization of the pseudomorphic to stable phase transition of Fe<sub>1-x</sub>Si on Si(111)**  
N. Onda, H. Siringhaus, S. Concalves-Conto, C. Schwarz, E. Muller-Gubler, H. von Kanel  
Edited by: Atwater, H.A.; Chason, E.; Grabow, M.H.; et al.  
Evolution of Surface and Thin Film Microstructure Symposium, Boston, MA, USA, 30 Nov.-4 Dec. 1992  
Evolution of Surface and Thin Film Microstructure Symposium (1993) 581-4
152. **Epitaxy of fluorite-structure silicides: metastable cubic FeSi/sub 2/ on Si(111)**  
N. Onda; J. Henz, E. Muller; K.A. Mader, H. von Kanel  
Appl. Surf. Sci. **56-58**, (1992) 421-6
153. **Occurrence of two ordered structures in Si-Ge systems**  
E. Muller; H.-U. Nissen, K.A. Mader, M. Ospelt, H. von Kanel  
Phil. Mag. Lett. **64**, (1991) 183

154. **Silicon heteroepitaxy: interface structure and physical properties**  
H. von Kanel; E. Muller; H.-U. Nissen, W. Bacsa, M. Ospelt, K.A. Mader, R. Stalder, A. Baldereschi  
J. Crystal Growth **111**, (1991) 889-96
155. **Structural and electrical investigation of an epitaxial metallic FeSi<sub>2</sub> phase on Si(111)**  
N. Onda, J. Henz, E. Muller, H. von Kanel, C. Schwarz, R.E. Pixley  
Autumn meeting of the Soc. Suisse Phys., Geneva, OCT 03-04, 1990  
Helvetica Physica Acta **64** (1991) 197-198
156. **Interface structural characterization of strained layer (001) Si/sub m/Ge/sub n/ superlattices by Raman spectroscopy**  
W. Bacsa, M. Ospelt-M, J. Henz, H. von Kanel, E. Muller, P. Wachter  
Proc.-of-the-SPIE, Int. Soc. Opt. Engineering. **1284** (1990).195-206
157. **Temperature stability of interfacial ordering in strained layer Si-Ge superlattices**  
E. Muller, H.-U. Nissen, M. Ospelt, H. von Kanel  
Helvetica-Physica-Acta. **63** (1990) 481-2
158. **Epitaxy of metal silicides**  
H. von Kanel; J. Henz M. Ospelt, J. Hugi-, E. Muller, N. Onda, A. Gruhle  
Thin Solid Films **184** (1990) 295-308
159. **Chemical ordering and boundary structure in crystalline Si-Ge superlattices**  
E. Muller, H.-U. Nissen, M. Ospelt, H. von Kanel, P. Stadelmann  
Thin Solid Films **183** (1989) 165
160. **Chemical ordering and boundary structure in strained-layer Si-Ge superlattices**  
E. Muller, H.-U. Nissen, M. Ospelt, H. von Kanel  
Phys. Rev. Lett. **63** (1989) 1819